TOSHIBA Photocoupler GaAlAs Ired & Photo IC

# **TLP559**

Digital Logic Ground Isolation
Line Receiver
Microprocessor System Interfaces
Switching Power Supply Feedback Control
Transistor Inverter

The TOSHIBA TLP559 consists of a GaAlAs high–output light emitting diode and a high speed detector of one chip photo diode–transistor. This unit is 8–lead DIP package.

TLP559 has no internal base connection, and a faraday shield integrated on the photodetector chip provides an effective common mode noise transient immunity.

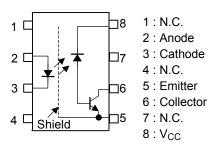
So this is suitable for application in noisy environmental condition.

- Isolation voltage: 2500Vrms (min.)
- Switching speed:  $t_{pHL} = 0.3\mu s$  (typ.)  $t_{pLH} = 0.5\mu s$  (typ.) (R<sub>L</sub> = 1.9k $\Omega$ )
- TTL compatible
- UL recognized: UL1577, file No.E67349

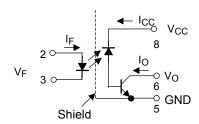
# Unit in mm 8 7 6 5 0 0 1 1 2 3 4 9.66 ± 0.25 0.25 0.05 0.25 0.05 0.25 0.05 7.85 ~ 8.80 11-10C4 TOSHIBA 11-10C4

Weight: 0.54g

### Pin Configuration (top view)



### **Schematic**



### Absolute Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit	
TED	Forward current	(Note 1)	l <sub>F</sub>	25	mA
	Pulse forward current	(Note 2)	I <sub>FP</sub>	50	mA
	Peak transient forward current	(Note 3)	I <sub>FPT</sub>	1	Α
	Reverse voltage		V <sub>R</sub>	5	V
	Diode power dissipation	(Note 4)	PD	45	mW
	Output current		IO	8	mA
ō	Peak output current		I <sub>OP</sub>	16	mA
Detector	Output voltage		V <sub>O</sub>	-0.5~15	V
ă	Supply voltage		V <sub>CC</sub>	-0.5~15	V
	Output power dissipation	(Note 5)	PO	100	mW
Оре	erating temperature range		T <sub>opr</sub>	-55~100	°C
Sto	Storage temperature range		T <sub>stg</sub>	-55~125	°C
Lea	Lead solder temperature (10s) (Note 6)		T <sub>sol</sub>	260	°C
Isol	Isolation voltage (AC, 1 min., R.H. ≤ 60%) (Note 7)		BVS	2500	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- (Note 1) Derate 0.8mA above 70°C.
- (Note 2) 50% duty cycle,1ms pulse width. Derate 1.6mA / °C above 70°C.
- (Note 3) Pulse width  $\leq 1 \mu s$ , 300pps.
- (Note 4) Derate 0.9mW / °C above 70°C.
- (Note 5) Derate 2mW / °C above 70°C.
- (Note 6) Soldering portion of lead: up to 2mm from body of the devise.
- (Note 7) Device considered a two-terminal device: Pins 1, 2, 3 and 4 shorted together and pins 5, 6, 7 and 8 shorted together.

# **Electrical Characteristics (Ta = 25°C)**

Characteristic		Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 16mA	_	1.65	1.85	V
	Forward voltage temperature coefficient	ΔV <sub>F</sub> / ΔTa	I <sub>F</sub> = 16mA	_	-2	_	mV / °C
	Reverse current	$I_{R}$	V <sub>R</sub> = 5V	_	_	10	μΑ
	Capacitance between terminal	C <sub>T</sub>	V <sub>F</sub> = 0, f = 1MHz	-	45	_	pF
Detector	High level output current	I <sub>OH</sub> (1)	I <sub>F</sub> = 0mA, V <sub>CC</sub> = V <sub>O</sub> = 5.5V	_	3	500	nA
		I <sub>OH</sub> (2)	I <sub>F</sub> = 0mA, V <sub>CC</sub> = V <sub>O</sub> = 15V	_	_	5	
		Іон	I <sub>F</sub> = 0mA, V <sub>CC</sub> = 15V V <sub>O</sub> = 15V, Ta = 70°C	_	_	50	μA
	High level supply voltage	Icch	I <sub>F</sub> = 0mA, V <sub>CC</sub> = 15V	_	0.01	1	μΑ
Coupled	Current transfer ratio	I <sub>O</sub> / I <sub>F</sub>		20	40	_	%
	Low level output voltage	V <sub>OL</sub>	I <sub>F</sub> = 16mA, V <sub>CC</sub> = 4.5V I <sub>O</sub> = 2.4mA	_	_	0.4	V
	Resistance (input-output)	R <sub>S</sub>	R.H. ≤ 60%, V <sub>S</sub> = 500V <sub>DC</sub> (Note 7)	5×10 <sup>10</sup>	10 <sup>14</sup>		Ω
	Capacotance (input-output)	CS	$V_S = 0$ , $f = 1MHz$ (Note 7)	_	0.8	_	pF

# Switching Characteristics (Ta = 25°C, V<sub>CC</sub> = 5V)

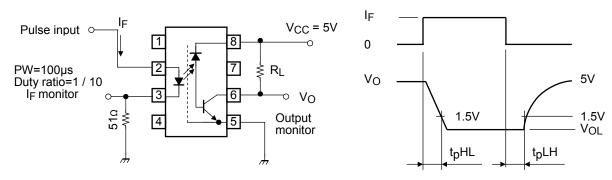
Characteristic		Symbol	Test Cir– cuit	Test Condition	Min.	Тур.	Max.	Unit
Propagation delay time	(H→ L)	t <sub>pHL</sub>	1	$I_F$ = 16mA, $R_L$ = 1.9kΩ	_	0.2	0.8	μs
Propagation delay time	(L→ H)	t <sub>pLH</sub>	'		_	0.3	0.8	μs
Common mode transient immunity at logic high output	(Note 8)	CM <sub>H</sub>	- 2	$I_F = 0$ mA, $V_{CM} = 400V_{p-p}$ RL = 4.1k $\Omega$	2000	10000	_	V / µs
Common mode transient immunity at logic high output	(Note 8)	CML		$I_F = 16\text{mA}, V_{CM} = 400V_{p-p}$ R <sub>L</sub> = 4.1k $\Omega$	-2000	-10000	-	V / µs

(Note 8) CM<sub>L</sub> is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic low state ( $V_O < 0.8V$ ).

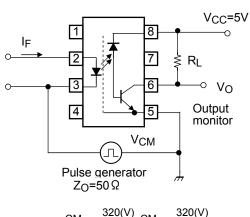
 $CM_H$  is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic high state ( $V_O < 2.0V$ ).

(Note 9) Maximum electrostatic discharge voltage for any pins: 100V (C = 200pF, R = 0)

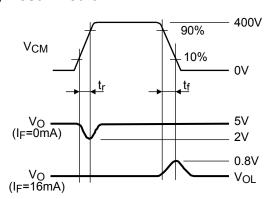
# **Test Circuit 1: Switching Time Test Circuit**

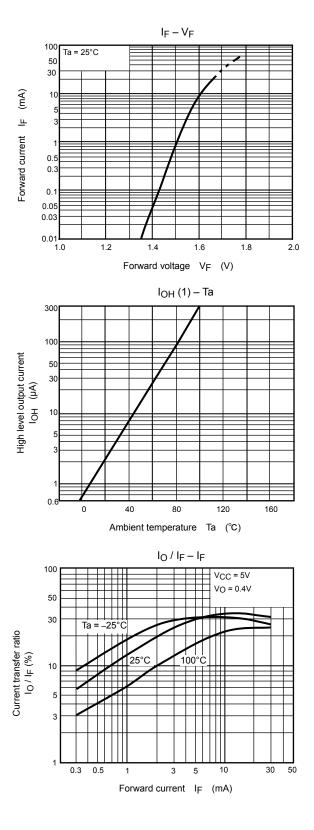


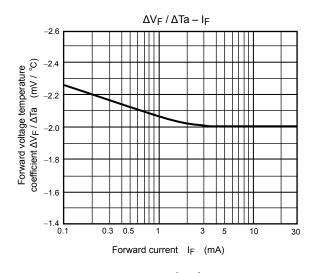
# **Test Circuit 2: Common Mode Noise Immunity Test Circuit**

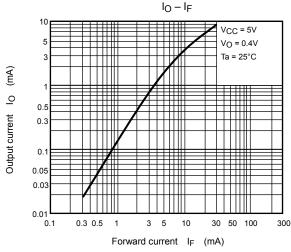


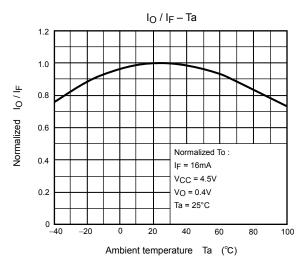
$$\text{CM}_{H} = \frac{320(\text{V})}{t_{\text{\Gamma}}(\mu s)}, \text{CM}_{L} = \frac{320(\text{V})}{t_{\text{f}}(\mu s)}$$

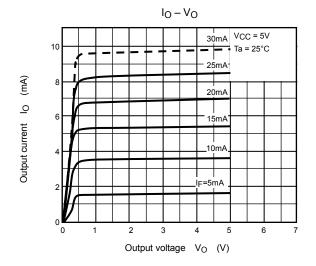


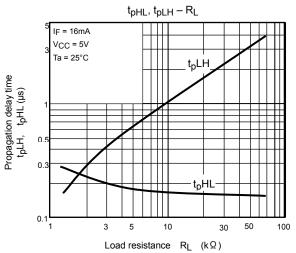


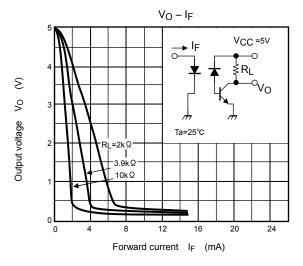












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